



4N60-S

Power MOSFET

4A, 600V N-CHANNEL POWER MOSFET

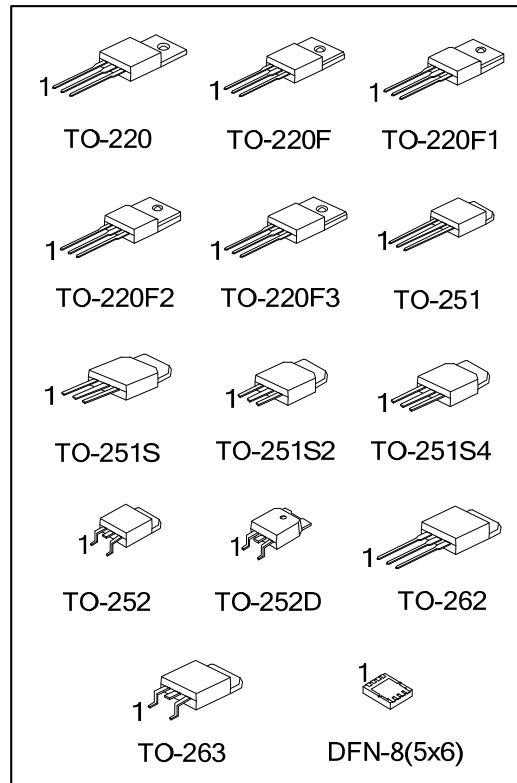
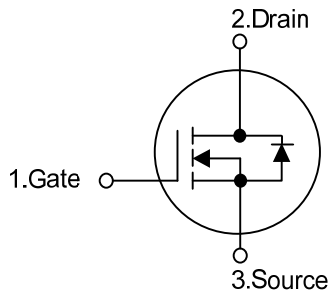
DESCRIPTION

The UTC **4N60-S** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 2.5\Omega$ @ $V_{GS}=10V$, $I_D=2.2A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, high RuggednessA

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
4N60L-TA3-T	4N60G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
4N60L-TF1-T	4N60G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
4N60L-TF2-T	4N60G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	Tube
4N60L-TF3-T	4N60G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	Tube
4N60L-TF3T-T	4N60G-TF3T-T	TO-220F3	G	D	S	-	-	-	-	-	Tube
4N60L-TM3-T	4N60G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
4N60L-TMS-T	4N60G-TMS-T	TO-251S	G	D	S	-	-	-	-	-	Tube
4N60L-TMS2-T	4N60G-TMS2-T	TO-251S2	G	D	S	-	-	-	-	-	Tube
4N60L-TMS4-T	4N60G-TMS4-T	TO-251S4	G	D	S	-	-	-	-	-	Tube
4N60L-TN3-R	4N60G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
4N60L-TND-R	4N60G-TND-R	TO-252D	G	D	S	-	-	-	-	-	Tape Reel
4N60L-T2Q-T	4N60G-T2Q-T	TO-262	G	D	S	-	-	-	-	-	Tube
4N60L-TQ2-R	4N60G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
4N60L-TQ2-T	4N60G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
-	4N60G-K08-5060-R	DFN-8(5×6)	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N60L-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2 TF3: TO-220F, TF3T: TO-220F3, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TN3: TO-252, TMS4: TO-251S4, TND: TO-252D, T2Q: TO-262, TQ2: TO-263, K08-5060: DFN-8(5×6)</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING

PACKAGE	MARKING
TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3 TO-251 TO-251S TO-251S2 TO-251S4 TO-252 TO-252D TO-262 TO-263	<p>UTC 4N60</p> <p>Lot Code ← → Data Code</p> <p>1</p> <p>L: Lead Free G: Halogen Free</p>
DFN-8(5×6)	<p>UTC 4N60</p> <p>Lot Code ← → Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	600	V
Gate-Source Voltage	V_{GSS}	± 30	V
Avalanche Current (Note 2)	I_{AR}	4.4	A
Drain Current	Continuous	I_D	4.0
	Pulsed (Note 2)	I_{DM}	16
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	100
	Repetitive (Note 2)	E_{AR}	10.6
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262/TO-263 TO-220F/TO-220F1 TO-220F2/TO-220F3	P_D	106
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		50
	DFN-8(5x6)		30
			W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L = 30\text{mH}$, $I_{AS} = 2.6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-262/TO-263 TO-220F/TO-220F1 TO-220F2/TO-220F3	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		110	
	DFN-8(5x6)		75 (Note)	
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	1.18	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1 TO-220F3		3.47	
	TO-220F2		3.28	
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.5	
	DFN-8(5x6)		4.17 (Note)	

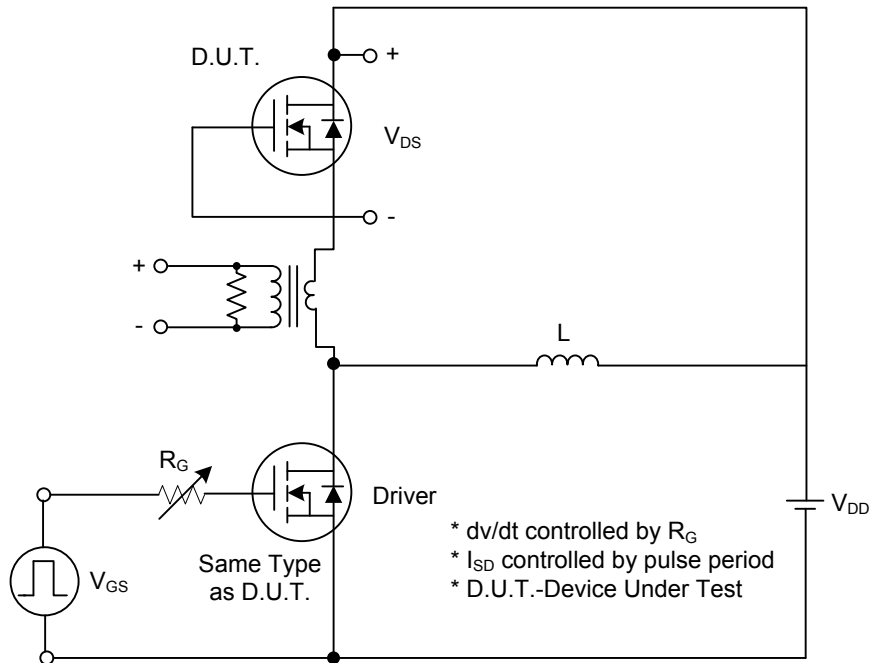
Note: Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

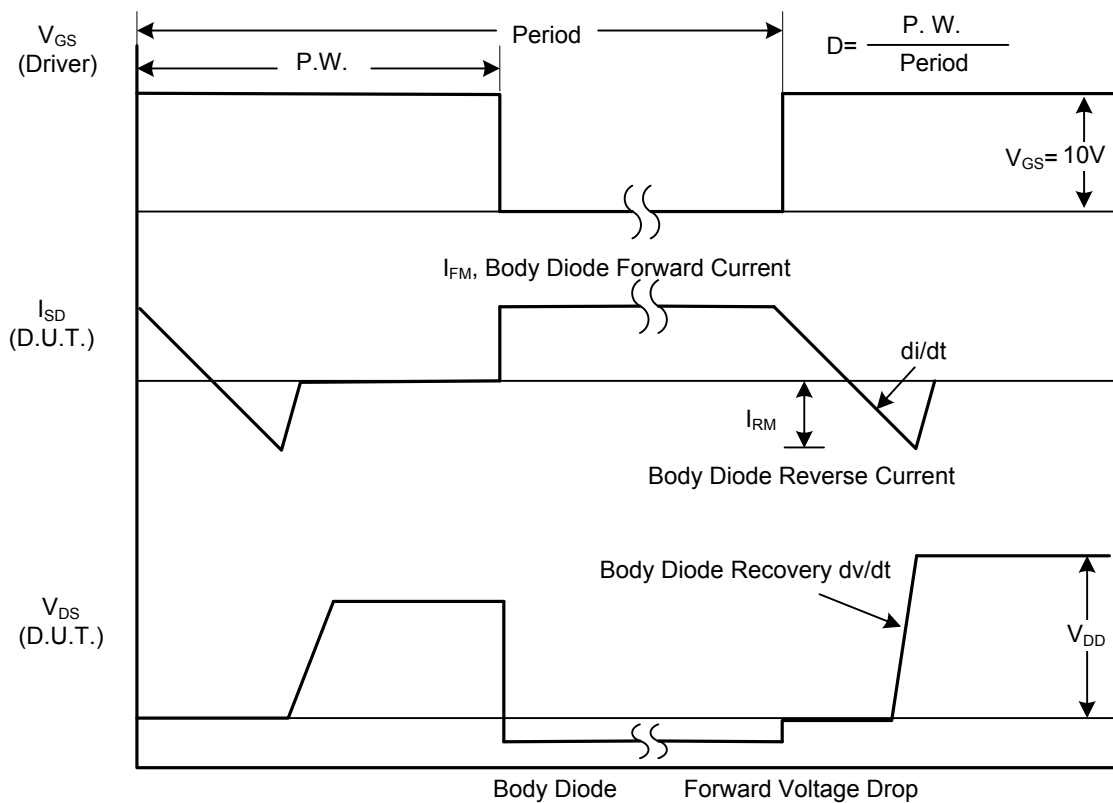
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	μA	
Gate-Source Leakage Current	Forward	I _{GSS}			100	nA	
	Reverse				V _{GS} = 30V, V _{DS} = 0V	-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	3.0		5.0	V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2.2A		2.2	2.5	Ω	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		440	520	pF	
Output Capacitance	C _{OSS}				45	60	pF
Reverse Transfer Capacitance	C _{RSS}				8	11	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 300V, I _D = 4.0A, R _G = 25Ω (Note 1, 2)		40	60	ns	
Turn-On Rise Time	t _R			40	60	ns	
Turn-Off Delay Time	t _{D(OFF)}			35	55	ns	
Turn-Off Fall Time	t _F			80	100	ns	
Total Gate Charge	Q _G	V _{DS} = 480V, I _D = 4.0A, V _{GS} = 10V (Note 1, 2)		35		nC	
Gate-Source Charge	Q _{GS}			5		nC	
Gate-Drain Charge	Q _{GD}			3		nC	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 4.4A			1.4	V	
Maximum Continuous Drain-Source Diode Forward Current	I _S				4.4	A	
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				17.6	A	
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _S = 4.4A, dI _F /dt = 100 A/μs (Note 1)		250		ns	
Reverse Recovery Charge	Q _{RR}				1.5		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

TEST CIRCUITS AND WAVEFORMS

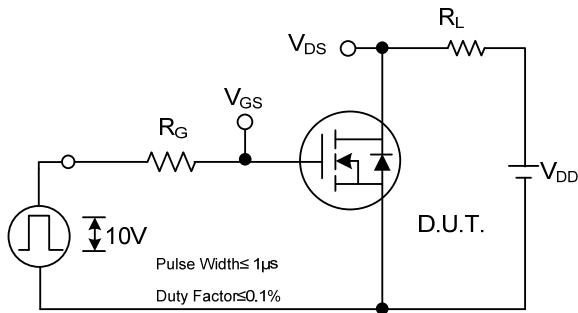


Peak Diode Recovery dv/dt Test Circuit

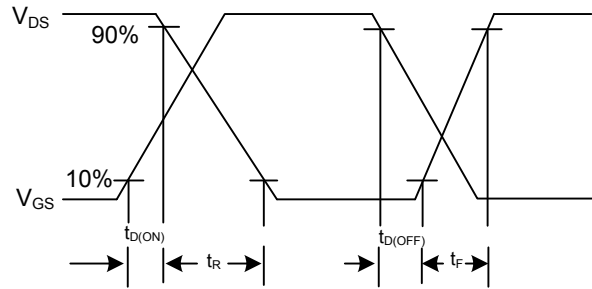


Peak Diode Recovery dv/dt Waveforms

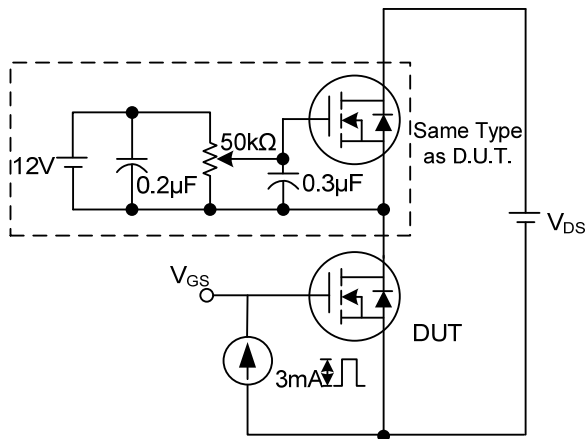
TEST CIRCUITS AND WAVEFORMS (Cont.)



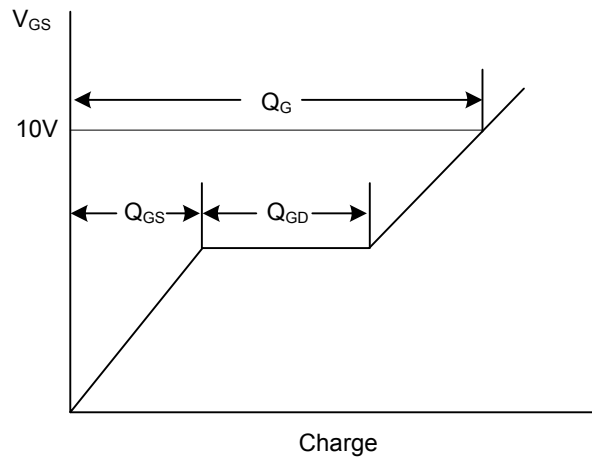
Switching Test Circuit



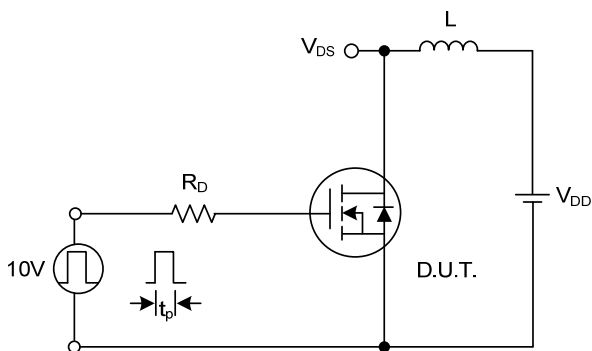
Switching Waveforms



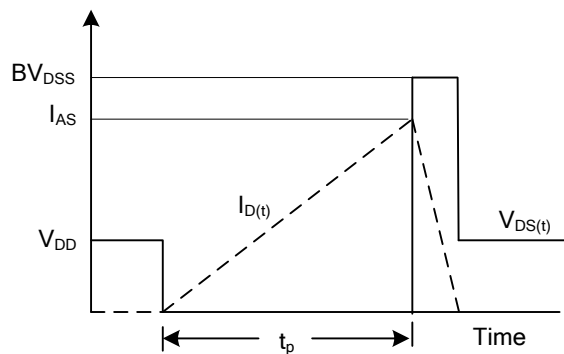
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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